

This listing of claims will replace all prior versions, all listings, of claims in the application:

LISTING OF CLAIMS

Claim 1 (currently amended)

A Thin-Film Transistor array structure, comprising:

a Thin-Film Transistor;

a data line coupled to a drain electrode of the Thin-Film Transistor;

a scanning line coupled to a gate electrode of the Thin-Film Transistor and crossed to the data line to form a plurality of rectangular pixels in matrix;

a pixel electrode formed at each of the pixels and coupled electrically connected to a source electrode of the Thin-Film Transistor, the pixel electrode having an edge parallel to the data line; and

an auxiliary electrode coupled electrically connected to the pixel electrode, wherein the edge of the pixel electrode is disposed on the auxiliary electrode.

Claim 2 (previously amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein a pattern constructed by the auxiliary electrode, the source electrode and the data line is designed as a mask.

Claim 3 (previously amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the auxiliary electrode is formed in an H-shaped pattern.

Claim 4 (previously amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the pixel electrode is coupled to the source electrode via a contact hole.

Claim 5 (previously amended)

The Thin-Film Transistor array structure as claimed in Claim 1, wherein the auxiliary electrode is coupled to the pixel electrode via a contact hole.

Claim 6 (Currently amended)

A Thin-Film Transistor array structure, comprising:

 a Thin-Film Transistor;

 a data line coupled to a drain electrode of the Thin-Film Transistor;

 a scanning line coupled to a gate electrode of the Thin-Film Transistor and crossed to the data line to form a plurality of rectangular pixels in matrix; and

 a pixel electrode formed at each of the pixels and coupled electrically connected to a source electrode of the Thin-Film Transistor via a contact hole, wherein ~~the an~~ edge of the pixel electrode is parallel to the data line and is disposed on the source electrode ~~which is extended to the region where the pixel electrode is next to the data line.~~

Claim 7 (Original)

The Thin-Film Transistor array structure as claimed in Claim 6, wherein a pattern constructed by the source electrode and the data line is designed as a mask.

Claim 8 (Original)

The Thin-Film Transistor array structure as claimed in Claim 6, wherein the source electrode is formed in a U-shaped pattern.

Claims 9-11 (Canceled)

Claim 12 (New)

A Thin-Film Transistor array structure, comprising:

 a Thin-Film Transistor having a drain electrode, a gate electrode and a source electrode;

 a first data line and a second data line, the first data line electrically connected to the drain electrode;

 a scanning line coupled to the gate electrode and crossing the first data line and the second data line;

 a pixel electrode arranged between the first data line and the second data line and electrically connected to the source electrode, the pixel electrode having a first edge and a second edge; and

an auxiliary electrode having a first portion disposed adjacent and parallel to the first data line, arranged at a first predetermined distance from the first data line and electrically connected to the pixel electrode, and a second portion disposed adjacent and parallel to the second data line, arranged at a second predetermined distance from the second data line and electrically connected to the pixel electrode,

wherein the first edge of the pixel electrode has a distance from the first data line greater than a distance between the first portion of the auxiliary electrode and the first data line, and the second edge of the pixel electrode has a distance from the second data line greater than a distance between the second portion of the auxiliary electrode and the second data line.

Claim 13 (New)

The Thin-Film Transistor array structure as claimed in claim 12, wherein a pattern formed by the first data line, the second data line, the first portion and the second portion of the auxiliary electrode is designed as a mask.

Claim 14 (New)

The Thin-Film Transistor array structure as claimed in claim 12, wherein the first portion and the second portion of the auxiliary electrode are electrically connected to the pixel electrode via the source electrode.

Claim 15 (New)

The Thin-Film Transistor array structure as claimed in claim 14, wherein the first portion and the second portion of the auxiliary electrode are an extended portion of the source electrode.

Claim 16 (New)

A Thin-Film Transistor array structure, comprising:

a first pixel and a second pixel separately arranged in a first exposed block and a second exposed block, each of the first pixel and second pixel comprising:

a first data line and a second data line separated by a predetermined distance,

a pixel electrode arranged between the first data line and the second data line,

a first electrode disposed adjacent and parallel to the first data line, arranged at a first predetermined distance from the first data line, and electrically connected to the pixel electrode, and

a second electrode disposed adjacent and parallel to the second data line, arranged at a second predetermined distance from the second data line and electrically connected to the pixel electrode,

wherein the first predetermined distance between the first electrode and the first data line at the first exposed block is the same as the first predetermined distance between the first electrode and the first data line at the second exposed block, and

wherein the second predetermined distance between the second electrode and the second data line at the first exposed block is the same as the second predetermined distance between the second electrode and the second data line at the second exposed block.

Claim 17 (New)

The Thin-Film Transistor array structure as claimed in claim 16, wherein a pattern formed by the first data line, the second data line, the first electrode, and second electrode, at the first exposed block or the second exposed block, is designed as a mask.

Claim 18 (New)

A Thin-Film Transistor array structure, comprising:

a first pixel and a second pixel separately arranged in a first exposed block and a second exposed block, each of the first pixel and second pixel comprising:

a first data line and a second data line separated by a predetermined distance,

a pixel electrode arranged between the first data line and the second data line,

a first electrode disposed adjacent and parallel to the first data line, arranged at a first predetermined distance from the first data line, and electrically connected to the pixel electrode, and

a second electrode disposed adjacent and parallel to the second data line, arranged at a second predetermined distance from the second data line and electrically connected to the pixel electrode,

wherein a first capacitance-coupling effect between the pixel electrode and the first data line at the first exposed block is the same as a first capacitance-coupling effect between the pixel electrode and the first data line at the second exposed block, and

wherein a second capacitance-coupling effect between the pixel electrode and the second data line at the first exposed block is the same as a second capacitance-coupling effect between the pixel electrode and the second data line at the second exposed block.

Claim 19 (New)

The Thin-Film Transistor array structure as claimed in claim 1, wherein the auxiliary electrode is disposed adjacent and parallel to the data line, at a predetermined distance from the data line.

Claim 20 (New)

The Thin-Film Transistor array structure as claimed in claim 6, wherein a portion of the source electrode extends along and is parallel to the data line, at a predetermined distance from the data line.

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